

# EVLYS LTD. - POWER SEMICONDUCTORS DEVICES - Wholesale and Retail.

## Fast Thyristor Type FDT32-400-12

Low switching losses / Low reverse recovery charge  
Distributed amplified gate for high  $di_T/dt$

Mean on-state current	$I_{TAV}$	400 A	
Repetitive peak off-state voltage	$V_{DRM}$	1000...1200 V	
Repetitive peak reverse voltage	$V_{RRM}$		
Turn-off time	$t_q$	10.0, 12.5, 16.0, 20.0 $\mu s$	
$V_{DRM}, V_{RRM}, V$	1000	1100	1200
Voltage code	10	11	12
$T_j, ^\circ C$	-60...+125		

### MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions
<b>ON-STATE</b>				
$I_{TAV}$	Mean on-state current	A	400 435 645	$T_c = 89^\circ C$ ; Double side cooled; $T_c = 85^\circ C$ ; Double side cooled; $T_c = 55^\circ C$ ; Double side cooled; 180° half-sine wave; 50 Hz
$I_{TRMS}$	RMS on-state current	A	628	$T_c = 89^\circ C$ ; Double side cooled; 180° half-sine wave; 50 Hz
$I_{TSM}$	Surge on-state current	kA	7.0 8.0	$T_j = T_{jmax}$ $T_j = 25^\circ C$ 180° half-sine wave; $t_p = 10$ ms; single pulse; $V_D = V_R = 0$ V; Gate pulse: $I_G = I_{FGM}$ ; $V_G = 20$ V; $t_{GP} = 50 \mu s$ ; $di_G/dt = 1$ A/ $\mu s$
			7.5 8.5	$T_j = T_{jmax}$ $T_j = 25^\circ C$ 180° half-sine wave; $t_p = 8.3$ ms; single pulse; $V_D = V_R = 0$ V; Gate pulse: $I_G = I_{FGM}$ ; $V_G = 20$ V; $t_{GP} = 50 \mu s$ ; $di_G/dt = 1$ A/ $\mu s$
$I^2t$	Safety factor	$A^2s \cdot 10^3$	240 320	$T_j = T_{jmax}$ $T_j = 25^\circ C$ 180° half-sine wave; $t_p = 10$ ms; single pulse; $V_D = V_R = 0$ V; Gate pulse: $I_G = I_{FGM}$ ; $V_G = 20$ V; $t_{GP} = 50 \mu s$ ; $di_G/dt = 1$ A/ $\mu s$
			230 290	$T_j = T_{jmax}$ $T_j = 25^\circ C$ 180° half-sine wave; $t_p = 8.3$ ms; single pulse; $V_D = V_R = 0$ V; Gate pulse: $I_G = I_{FGM}$ ; $V_G = 20$ V; $t_{GP} = 50 \mu s$ ; $di_G/dt = 1$ A/ $\mu s$
<b>BLOCKING</b>				
$V_{DRM}, V_{RRM}$	Repetitive peak off-state and Repetitive peak reverse voltages	V	1000...1200	$T_{jmin} < T_j < T_{jmax}$ ; 180° half-sine wave; 50 Hz; Gate open
$V_{DSM}, V_{RSM}$	Non-repetitive peak off-state and Non-repetitive peak reverse voltages	V	1100...1300	$T_{jmin} < T_j < T_{jmax}$ ; 180° half-sine wave; single pulse; Gate open
$V_D, V_R$	Direct off-state and Direct reverse voltages	V	$0.6 \cdot V_{DRM}$ $0.6 \cdot V_{RRM}$	$T_j = T_{jmax}$ ; Gate open

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<b>TRIGGERING</b>				
$I_{FGM}$	Peak forward gate current	A	6	$T_j = T_{j\max}$
$V_{RGM}$	Peak reverse gate voltage	V	5	
$P_G$	Gate power dissipation	W	3	$T_j = T_{j\max}$ for DC gate current
<b>SWITCHING</b>				
$(di_T/dt)_{crit}$	Critical rate of rise of on-state current non-repetitive (f=1 Hz)	A/ $\mu$ s	1600	$T_j = T_{j\max}$ ; $V_D = 0.67 \cdot V_{DRM}$ ; $I_{TM} = 1100$ A; Gate pulse: $I_G = I_{FGM}$ ; $V_G = 20$ V; $t_{GP} = 50$ $\mu$ s; $di_G/dt = 2$ A/ $\mu$ s
<b>THERMAL</b>				
$T_{stg}$	Storage temperature	$^{\circ}$ C	-60...+50	
$T_j$	Operating junction temperature	$^{\circ}$ C	-60...+125	
<b>MECHANICAL</b>				
F	Mounting force	kN	9.0...11.0	
a	Acceleration	m/s <sup>2</sup>	50	Device clamped

## CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
<b>ON-STATE</b>					
$V_{TM}$	Peak on-state voltage, max	V	2.40	$T_j = 25$ $^{\circ}$ C; $I_{TM} = 1256$ A	
$V_{T(TO)}$	On-state threshold voltage, max	V	1.430	$T_j = T_{j\max}$ ;	
$r_T$	On-state slope resistance, max	m $\Omega$	0.812	$0.5 \pi I_{TAV} < I_T < 1.5 \pi I_{TAV}$	
$I_H$	Holding current, max	mA	500	$T_j = 25$ $^{\circ}$ C; $V_D = 12$ V; Gate open	
<b>BLOCKING</b>					
$I_{DRM}, I_{RRM}$	Repetitive peak off-state and Repetitive peak reverse currents, max	mA	50	$T_j = T_{j\max}$ ; $V_D = V_{DRM}$ ; $V_R = V_{RRM}$	
$(dv_D/dt)_{crit}$	Critical rate of rise of off-state voltage <sup>1)</sup> , min	V/ $\mu$ s	200, 320, 500, 1000, 1600, 2000, 2500	$T_j = T_{j\max}$ ; $V_D = 0.67 \cdot V_{DRM}$ ; Gate open	
<b>TRIGGERING</b>					
$V_{GT}$	Gate trigger direct voltage, max	V	3.00 2.50 1.50	$T_j = T_{j\min}$ $T_j = 25$ $^{\circ}$ C $T_j = T_{j\max}$	$V_D = 12$ V; $I_D = 3$ A; Direct gate current
$I_{GT}$	Gate trigger direct current, max	mA	500 300 150	$T_j = T_{j\min}$ $T_j = 25$ $^{\circ}$ C $T_j = T_{j\max}$	
$V_{GD}$	Gate non-trigger direct voltage, min	V	0.40	$T_j = T_{j\max}$ ; $V_D = 0.67 \cdot V_{DRM}$ ;	
$I_{GD}$	Gate non-trigger direct current, min	mA	40.00	Direct gate current	
<b>SWITCHING</b>					
$t_{gd}$	Delay time, max	$\mu$ s	0.60	$T_j = 25$ $^{\circ}$ C; $V_D = 600$ V; $I_{TM} = I_{TAV}$ ; $di/dt = 200$ A/ $\mu$ s;	
$t_{gt}$	Turn-on time <sup>2)</sup> , max	$\mu$ s	1.25, 1.60, 2.00, 2.50	Gate pulse: $I_G = I_{FGM}$ ; $V_G = 20$ V; $t_{GP} = 50$ $\mu$ s; $di_G/dt = 2$ A/ $\mu$ s	
$t_q$	Turn-off time <sup>3)</sup> max	$\mu$ s	10.0, 12.5, 16.0, 20.0	$dv_D/dt = 50$ V/ $\mu$ s	$T_j = T_{j\max}$ ; $I_{TM} = 400$ A; $di_R/dt = -10$ A/ $\mu$ s; $V_R = 100$ V; $V_D = 0.67 V_{DRM}$
			12.5, 16.0, 20.0, 25.0	$dv_D/dt = 200$ V/ $\mu$ s	
$Q_{rr}$	Total recovered charge, max	$\mu$ C	100	$T_j = T_{j\max}$ ; $I_{TM} = 400$ A;	
$t_{rr}$	Reverse recovery time, max	$\mu$ s	3.2	$di_R/dt = -50$ A/ $\mu$ s;	
$I_{rrM}$	Peak reverse recovery current, max	A	80	$V_R = 100$ V	

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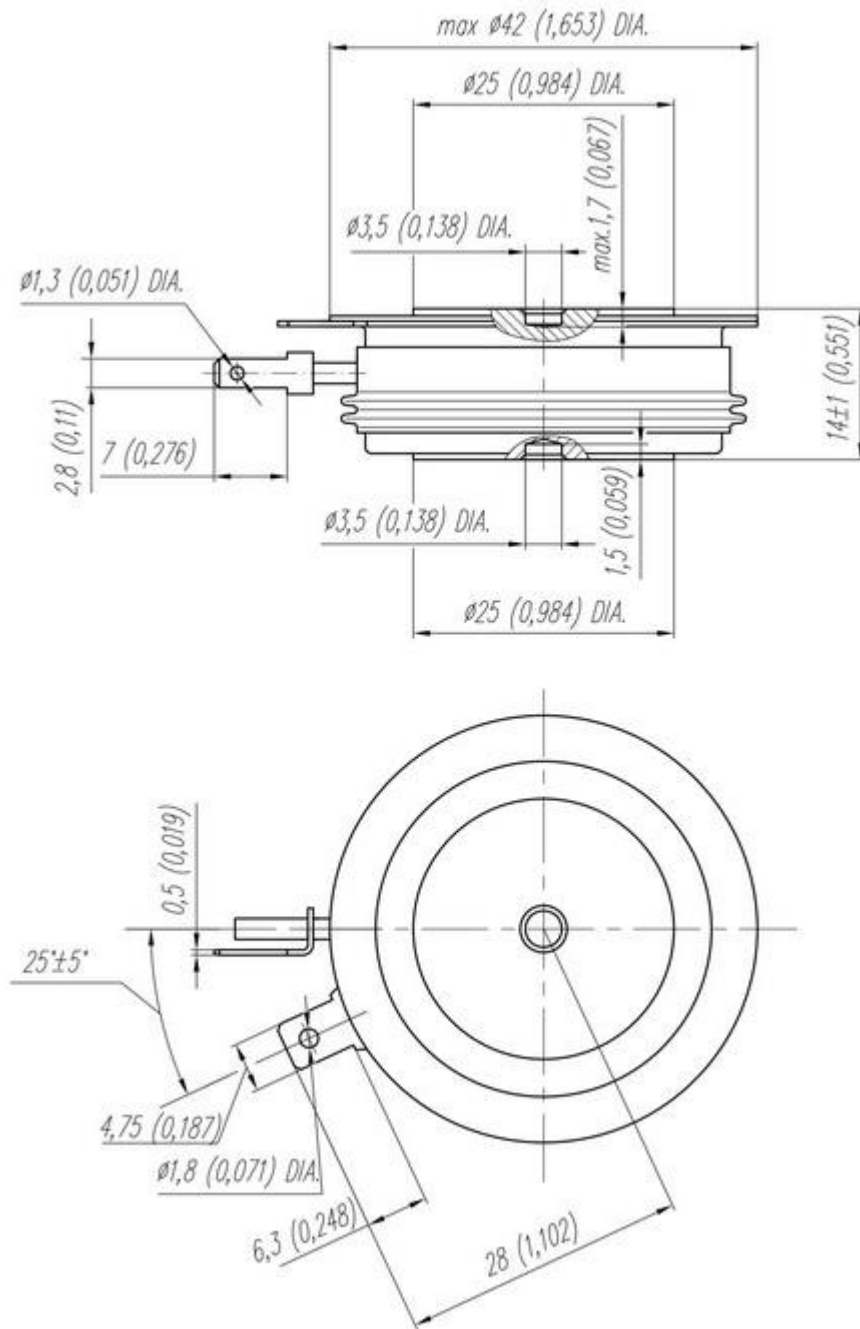
<b>THERMAL</b>					
$R_{thjc}$	Thermal resistance, junction to case, max	°C/W	0.0400	Direct current	Double side cooled
$R_{thjc-A}$			0.0880		Anode side cooled
$R_{thjc-K}$			0.0720		Cathode side cooled
$R_{thck}$	Thermal resistance, case to heatsink, max	°C/W	0.0060	Direct current	
<b>MECHANICAL</b>					
w	Weight, max	g	92		
$D_s$	Surface creepage distance	mm (inch)	10.30 (0.405)		
$D_a$	Air strike distance	mm (inch)	6.30 (0.248)		

<b>PART NUMBERING GUIDE</b>								<b>NOTES</b>																							
FDT	32	400	12	7	7	5		1) Critical rate of rise of off-state voltage																							
1	2	3	4	5	6	7		<table border="1" style="width: 100%;"> <thead> <tr> <th>Symbol of Group</th> <th>4</th> <th>5</th> <th>6</th> <th>7</th> <th>8</th> <th>8,5</th> <th>9</th> </tr> </thead> <tbody> <tr> <td><math>(dv_D/dt)_{crit}</math>, V/<math>\mu</math>S</td> <td>200</td> <td>320</td> <td>500</td> <td>1000</td> <td>1600</td> <td>2000</td> <td>2500</td> </tr> </tbody> </table>								Symbol of Group	4	5	6	7	8	8,5	9	$(dv_D/dt)_{crit}$ , V/ $\mu$ S	200	320	500	1000	1600	2000	2500
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## OVERALL DIMENSIONS

Package type: T.B2



All dimensions in millimeters (inches)

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